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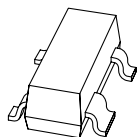
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Kind regards,

Team Nexperia



BCV61

NPN general-purpose double transistors

Rev. 04 — 18 December 2009

Product data sheet

1. Product profile

1.1 General description

NPN general-purpose double transistors in a small SOT143B Surface-Mounted Device (SMD) plastic package.

Table 1. Product overview

Type number	Package		PNP complement
	NXP	JEITA	
BCV61	SOT143B	-	BCV62
BCV61A			BCV62A
BCV61B			BCV62B
BCV61C			BCV62C

1.2 Features

- Low current (max. 100 mA)
- Low voltage (max. 30 V)
- Matched pairs

1.3 Applications

- Applications with working point independent of temperature
- Current mirrors

2. Pinning information

Table 2. Pinning

Pin	Description	Simplified outline	Graphic symbol
1	collector TR2; base TR1 and TR2		
2	collector TR1		
3	emitter TR1		
4	emitter TR2		

006aaa842

3. Ordering information

Table 3. Ordering information

Type number	Package		
	Name	Description	Version
BCV61	-	plastic surface-mounted package; 4 leads	SOT143B
BCV61A			
BCV61B			
BCV61C			

4. Marking

Table 4. Marking codes

Type number	Marking code ^[1]
BCV61	1M*
BCV61A	1J*
BCV61B	1K*
BCV61C	1L*

- [1] * = -: made in Hong Kong
 * = p: made in Hong Kong
 * = t: made in Malaysia
 * = W: made in China

5. Limiting values

Table 5. Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134).

Symbol	Parameter	Conditions	Min	Max	Unit
Per transistor					
V_{CBO}	collector-base voltage	open emitter	-	30	V
V_{CEO}	collector-emitter voltage	open base	-	30	V
V_{EBS}	emitter-base voltage	$V_{CE} = 0$ V	-	6	V
I_C	collector current		-	100	mA
I_{CM}	peak collector current		-	200	mA
I_{BM}	peak base current		-	200	mA
Per device					
P_{tot}	total power dissipation	$T_{amb} \leq 25$ °C	^[1] -	250	mW
T_j	junction temperature		-	150	°C
T_{amb}	ambient temperature		-65	+150	°C
T_{stg}	storage temperature		-65	+150	°C

- [1] Device mounted on an FR4 Printed-Circuit Board (PCB).

6. Thermal characteristics

Table 6. Thermal characteristics

Symbol	Parameter	Conditions	Min	Typ	Max	Unit
$R_{th(j-a)}$	thermal resistance from junction to ambient	in free air	[1] -	-	500	K/W

[1] Device mounted on an FR4 PCB.

7. Characteristics

Table 7. Characteristics

$T_j = 25\text{ }^{\circ}\text{C}$ unless otherwise specified.

Symbol	Parameter	Conditions	Min	Typ	Max	Unit
Transistor TR1						
I_{CBO}	collector-base cut-off current	$V_{CB} = 30\text{ V};$ $I_E = 0\text{ A}$	-	-	15	nA
		$V_{CB} = 30\text{ V};$ $I_E = 0\text{ A};$ $T_j = 150\text{ }^{\circ}\text{C}$	-	-	5	μA
I_{EBO}	emitter-base cut-off current	$V_{EB} = 5\text{ V};$ $I_C = 0\text{ A}$	-	-	100	nA
h_{FE}	DC current gain	$V_{CE} = 5\text{ V};$ $I_C = 100\text{ }\mu\text{A}$	100	-	-	
		$V_{CE} = 5\text{ V};$ $I_C = 2\text{ mA}$	110	-	800	
V_{CEsat}	collector-emitter saturation voltage	$I_C = 10\text{ mA};$ $I_B = 0.5\text{ mA}$	-	90	250	mV
		$I_C = 100\text{ mA};$ $I_B = 5\text{ mA}$	-	200	600	mV
V_{BEsat}	base-emitter saturation voltage	$I_C = 10\text{ mA};$ $I_B = 0.5\text{ mA}$	[1] -	700	-	mV
		$I_C = 100\text{ mA};$ $I_B = 5\text{ mA}$	[1] -	900	-	mV
V_{BE}	base-emitter voltage	$I_C = 2\text{ mA};$ $V_{CE} = 5\text{ V}$	[2] 580	660	700	mV
		$I_C = 10\text{ mA};$ $V_{CE} = 5\text{ V}$	[2] -	-	770	mV
f_T	transition frequency	$V_{CE} = 5\text{ V};$ $I_C = 10\text{ mA};$ $f = 100\text{ MHz}$	100	-	-	MHz
C_c	collector capacitance	$V_{CB} = 10\text{ V};$ $I_E = I_C = 0\text{ A};$ $f = 1\text{ MHz}$	-	2.5	-	pF
NF	noise figure	$V_{CE} = 5\text{ V};$ $I_C = 200\text{ }\mu\text{A};$ $R_S = 2\text{ k}\Omega;$ $f = 1\text{ kHz};$ $B = 200\text{ Hz}$	-	-	10	dB

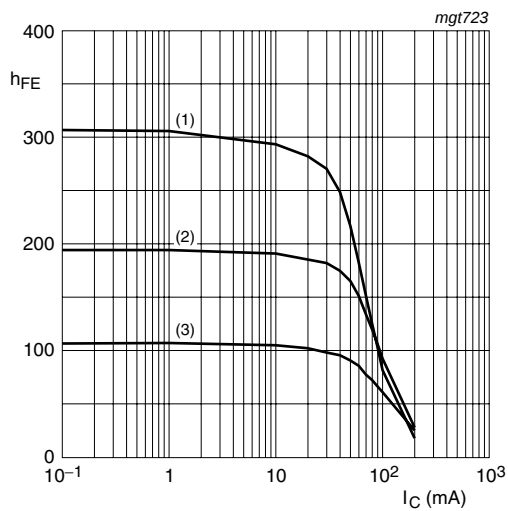
Table 7. Characteristics ...continued
 $T_j = 25\text{ }^{\circ}\text{C}$ unless otherwise specified.

Symbol	Parameter	Conditions	Min	Typ	Max	Unit
Transistor TR2						
V _{EBS}	emitter-base voltage	V _{CB} = 0 V; I _E = −250 mA	-	-	−1.8	V
		V _{CB} = 0 V; I _E = −10 μA	−400	-	-	mV
h _{FE}	DC current gain	V _{CE} = 5 V; I _C = 2 mA				
	BCV61		110	-	800	
	BCV61A		110	-	220	
	BCV61B		200	-	450	
	BCV61C		420	-	800	
Transistors TR1 and TR2						
I _{C1} /I _{E2}	current matching	I _{E2} = −0.5 mA; V _{CE1} = 5 V				
		T _{amb} ≤ 25 °C	0.7	-	1.3	
		T _{amb} ≤ 150 °C	0.7	-	1.3	
I _{E2}	emitter current 2	V _{CE1} = 5 V	[3]	-	−5	mA

[1] V_{BEsat} decreases by about 1.7 mV/K with increasing temperature.

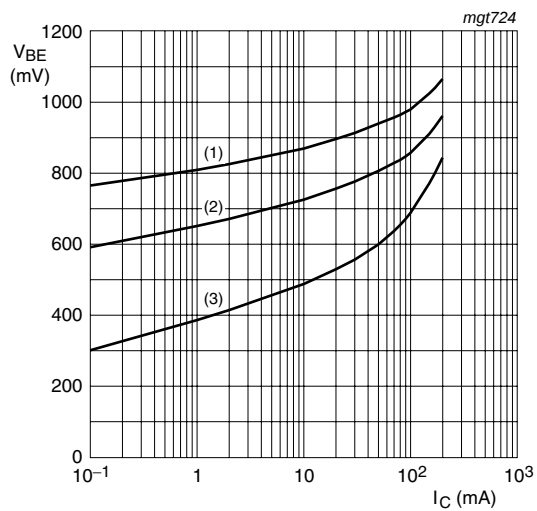
[2] V_{BE} decreases by about 2 mV/K with increasing temperature.

[3] Device, without emitter resistors, mounted on an FR4 PCB.



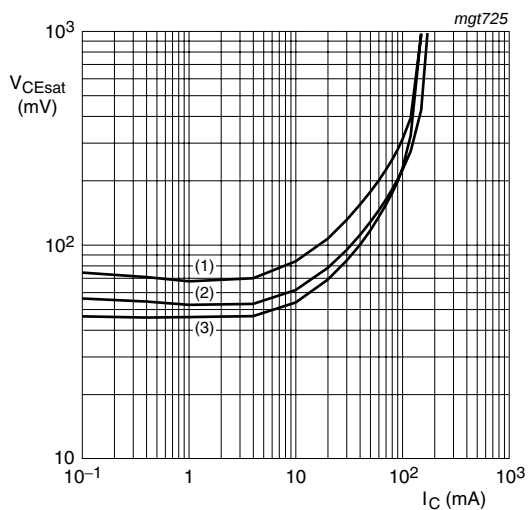
- $V_{CE} = 5\text{ V}$
- (1) $T_{amb} = 150\text{ }^{\circ}\text{C}$
 - (2) $T_{amb} = 25\text{ }^{\circ}\text{C}$
 - (3) $T_{amb} = -55\text{ }^{\circ}\text{C}$

Fig 1. BCV61A: DC current gain as a function of collector current; typical values



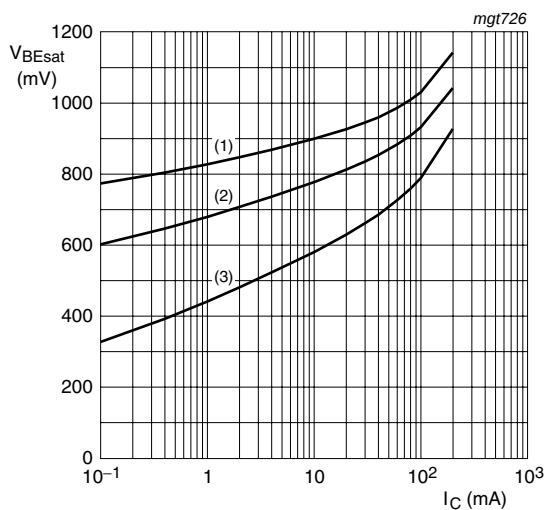
- $V_{CE} = 5\text{ V}$
- (1) $T_{amb} = -55\text{ }^{\circ}\text{C}$
 - (2) $T_{amb} = 25\text{ }^{\circ}\text{C}$
 - (3) $T_{amb} = 150\text{ }^{\circ}\text{C}$

Fig 2. BCV61A: Base-emitter voltage as a function of collector current; typical values



- $I_C/I_B = 20$
- (1) $T_{amb} = 150\text{ }^{\circ}\text{C}$
 - (2) $T_{amb} = 25\text{ }^{\circ}\text{C}$
 - (3) $T_{amb} = -55\text{ }^{\circ}\text{C}$

Fig 3. BCV61A: Collector-emitter saturation voltage as a function of collector current; typical values



- $I_C/I_B = 10$
- (1) $T_{amb} = -55\text{ }^{\circ}\text{C}$
 - (2) $T_{amb} = 25\text{ }^{\circ}\text{C}$
 - (3) $T_{amb} = 150\text{ }^{\circ}\text{C}$

Fig 4. BCV61A: Base-emitter saturation voltage as a function of collector current; typical values

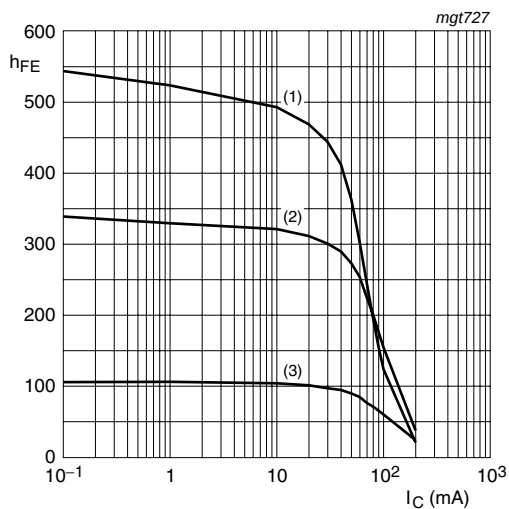


Fig 5. BCV61B: DC current gain as a function of collector current; typical values

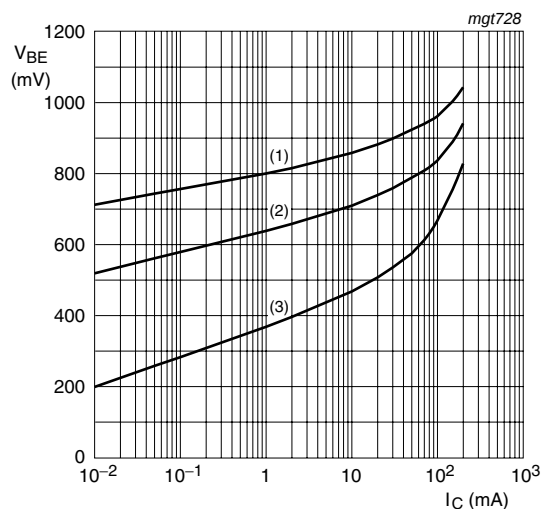


Fig 6. BCV61B: Base-emitter voltage as a function of collector current; typical values

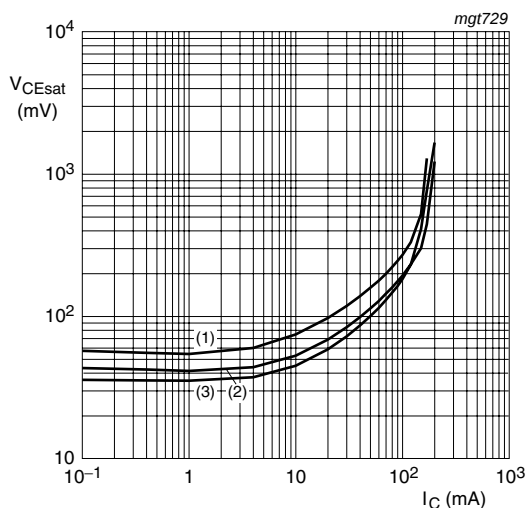


Fig 7. BCV61B: Collector-emitter saturation voltage as a function of collector current; typical values

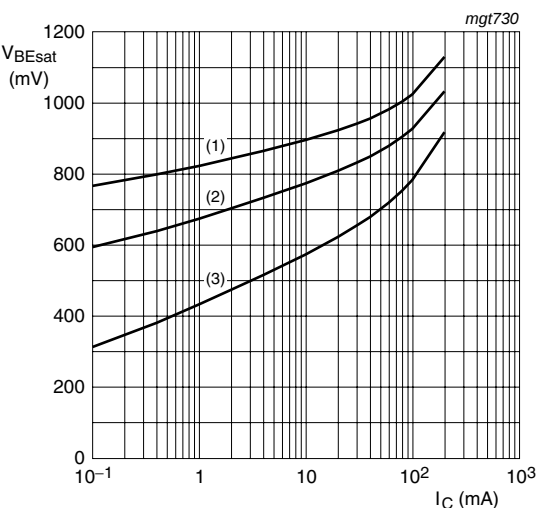
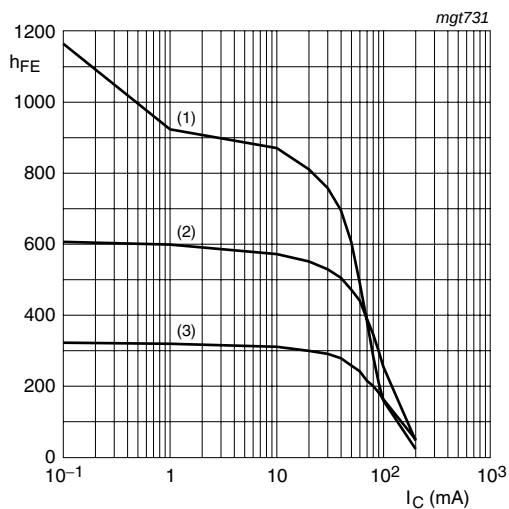
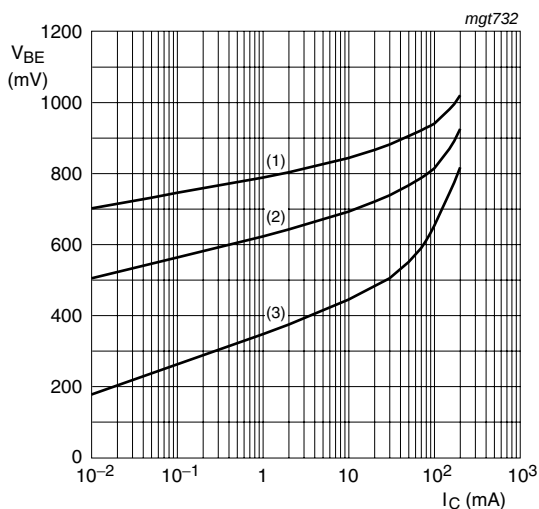


Fig 8. BCV61B: Base-emitter saturation voltage as a function of collector current; typical values



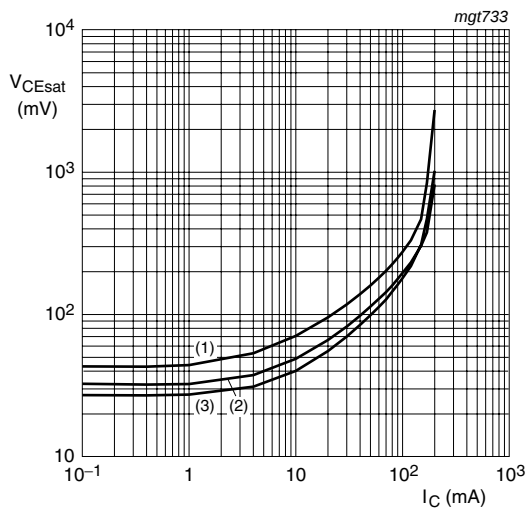
$V_{CE} = 5\text{ V}$
(1) $T_{amb} = 150\text{ }^{\circ}\text{C}$
(2) $T_{amb} = 25\text{ }^{\circ}\text{C}$
(3) $T_{amb} = -55\text{ }^{\circ}\text{C}$

Fig 9. BCV61C: DC current gain as a function of collector current; typical values



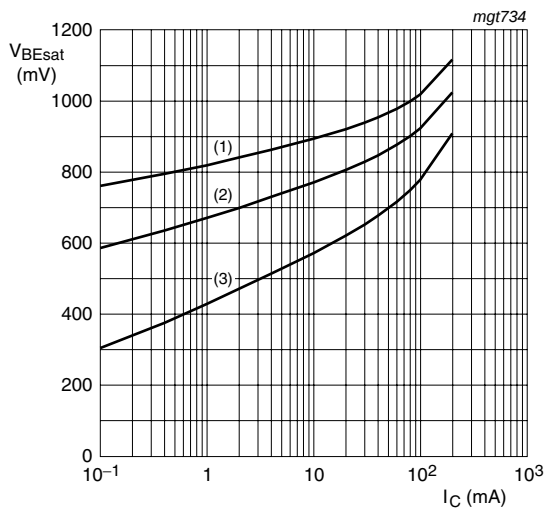
$V_{CE} = 5\text{ V}$
(1) $T_{amb} = -55\text{ }^{\circ}\text{C}$
(2) $T_{amb} = 25\text{ }^{\circ}\text{C}$
(3) $T_{amb} = 150\text{ }^{\circ}\text{C}$

Fig 10. BCV61C: Base-emitter voltage as a function of collector current; typical values



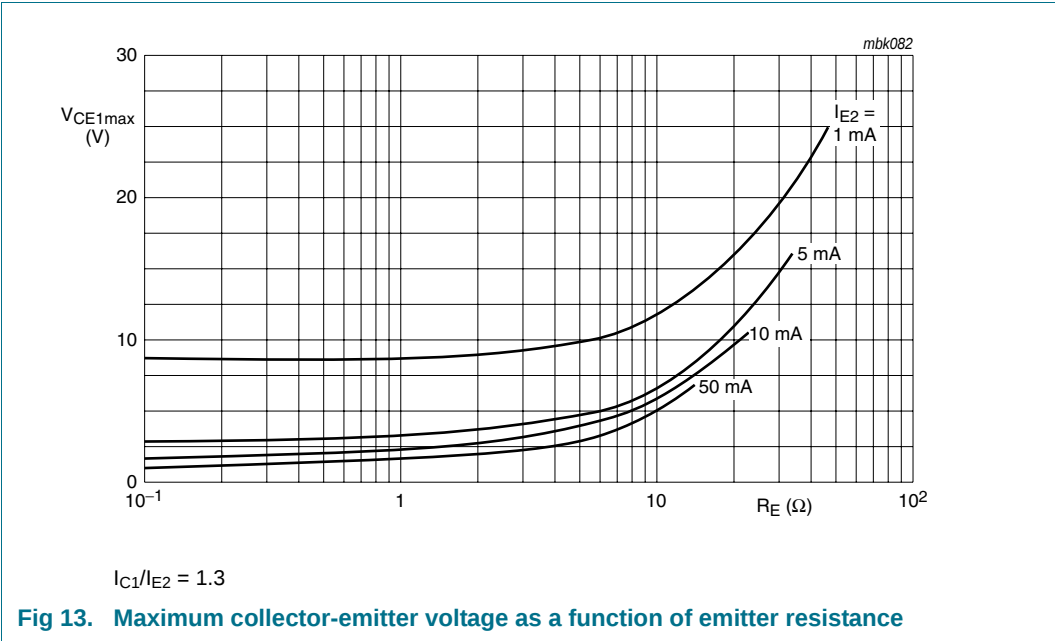
$I_C/I_B = 20$
(1) $T_{amb} = 150\text{ }^{\circ}\text{C}$
(2) $T_{amb} = 25\text{ }^{\circ}\text{C}$
(3) $T_{amb} = -55\text{ }^{\circ}\text{C}$

Fig 11. BCV61C: Collector-emitter saturation voltage as a function of collector current; typical values

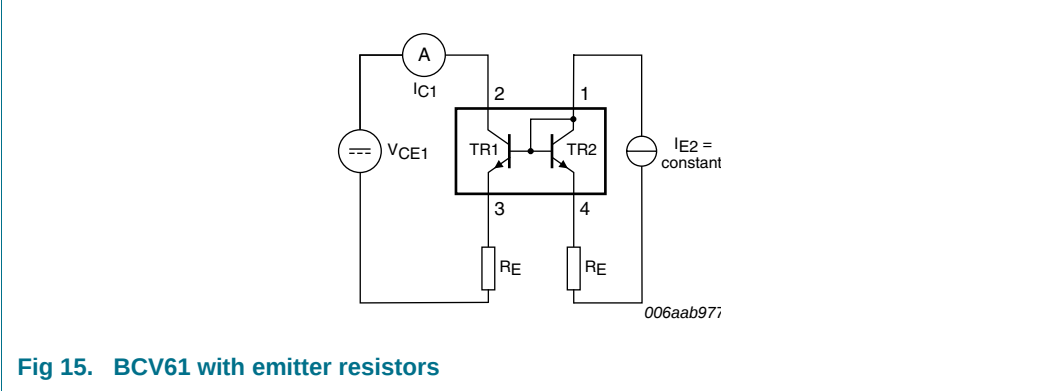
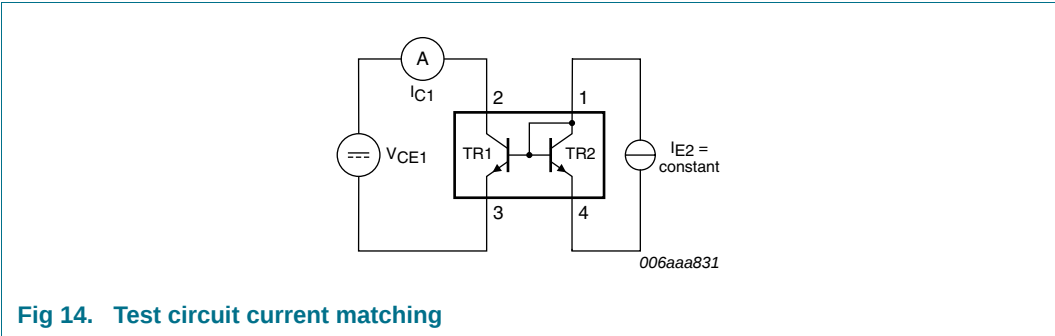


$I_C/I_B = 10$
(1) $T_{amb} = -55\text{ }^{\circ}\text{C}$
(2) $T_{amb} = 25\text{ }^{\circ}\text{C}$
(3) $T_{amb} = 150\text{ }^{\circ}\text{C}$

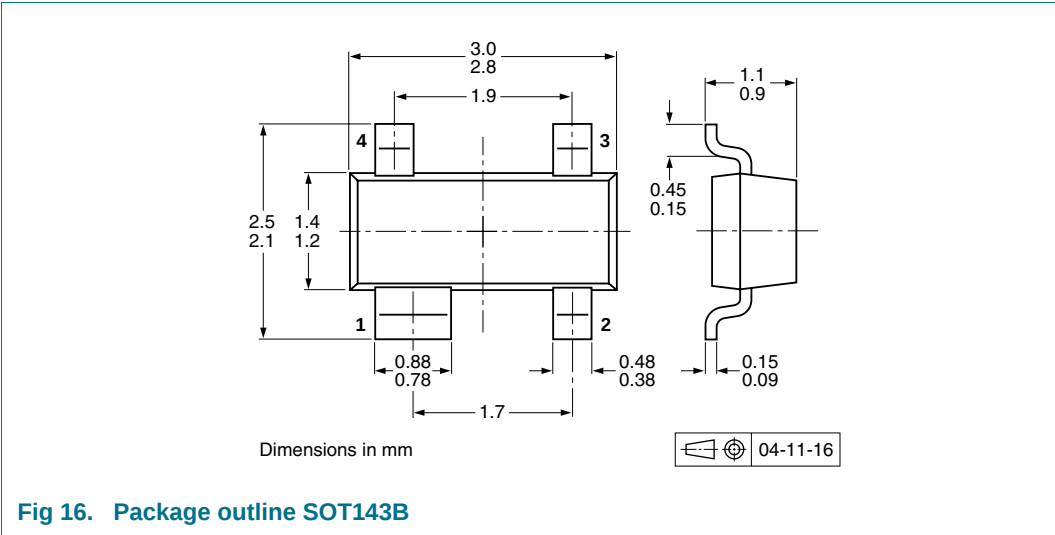
Fig 12. BCV61C: Base-emitter saturation voltage as a function of collector current; typical values



8. Test information



9. Package outline



10. Packing information

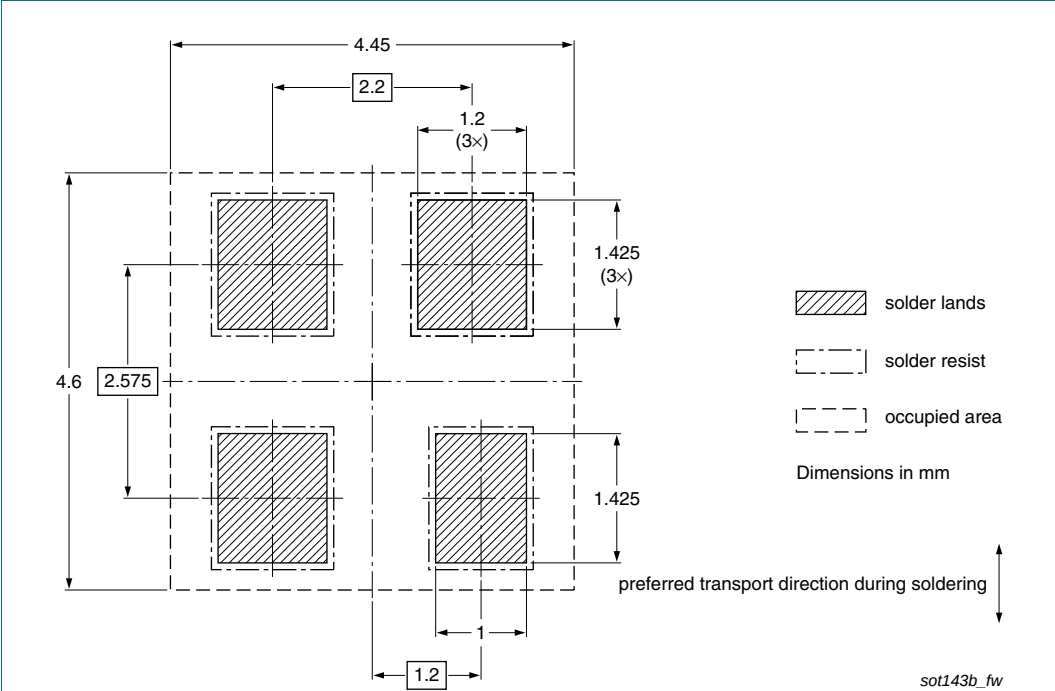
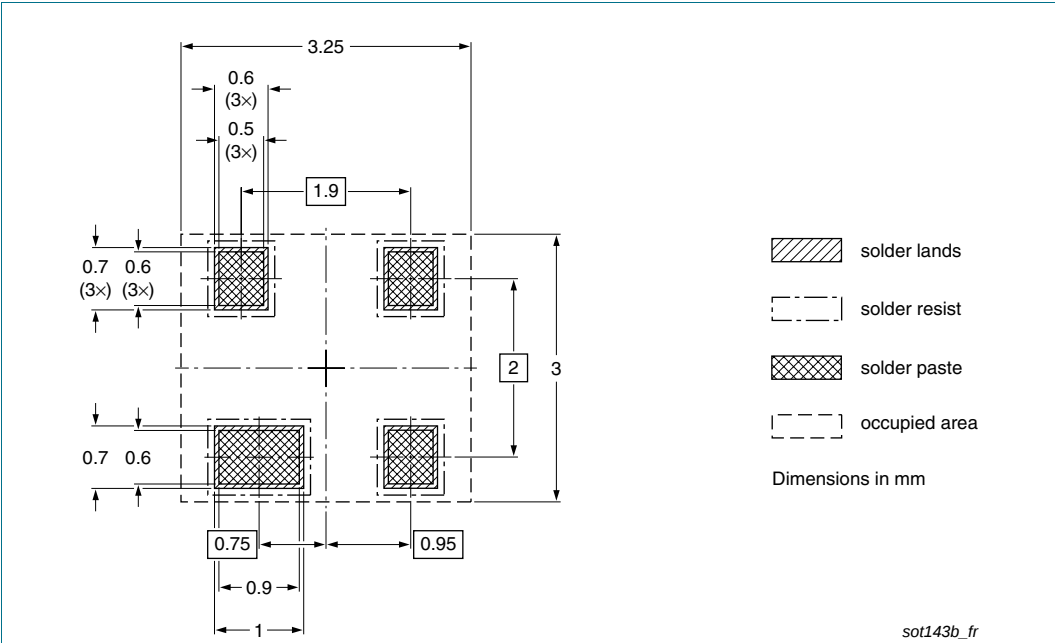
Table 8. Packing methods

The indicated -xxx are the last three digits of the 12NC ordering code.^[1]

Type number	Package	Description	Packing quantity	
			3000	10000
BCV61	SOT143B	4 mm pitch, 8 mm tape and reel	-215	-235
BCV61A				
BCV61B				
BCV61C				

[1] For further information and the availability of packing methods, see [Section 14](#).

11. Soldering



12. Revision history

Table 9. Revision history

Document ID	Release date	Data sheet status	Change notice	Supersedes
BCV61_4	20091218	Product data sheet	-	BCV61_3
Modifications:	• The format of this data sheet has been redesigned to comply with the new identity guidelines of NXP Semiconductors. • Legal texts have been adapted to the new company name where appropriate. • Section 3 "Ordering information": added • Section 4 "Marking": updated • Figure 1, 2, 3, 4, 5, 6, 7, 8, 9, 10, 11 and 12: added • Section 8 "Test information": added • Figure 16: superseded by minimized package outline drawing • Section 10 "Packing information": added • Section 11 "Soldering": added • Section 13 "Legal information": updated			
BCV61_3	19990408	Product specification	-	BCV61_CNV_2
BCV61_CNV_2	19970616	Product specification	-	-

13. Legal information

13.1 Data sheet status

Document status ^{[1][2]}	Product status ^[3]	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
Preliminary [short] data sheet	Qualification	This document contains data from the preliminary specification.
Product [short] data sheet	Production	This document contains the product specification.

[1] Please consult the most recently issued document before initiating or completing a design.

[2] The term 'short data sheet' is explained in section "Definitions".

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